

# **4V Drive Pch MOSFET**

# RSC002P03

#### Structure

Silicon P-channel MOSFET

### Features

- 1) Low on-resistance.
- 2) Low-voltage drive (4V).

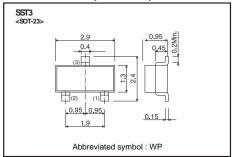
# Application

Switching

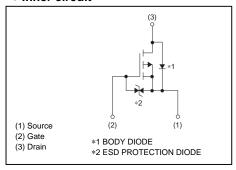
Packaging specifications

	Package	Taping	
Type	Code	T316	
	Basic ordering unit (pieces)	3000	
RSC002P0	0		

### • Dimensions (Unit : mm)



#### • Inner circuit



# ● Absolute maximum ratings (Ta = 25°C)

Parame	Symbol	Limits	Unit	
Drain-source voltage		$V_{DSS}$	-30	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current	Continuous	I <sub>D</sub>	±0.25	Α
	Pulsed	I <sub>DP</sub> *1	±0.5	Α
Power dissipation		P <sub>D</sub> *2	0.2	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

<sup>\*1</sup> Pw≤10µs, Duty cycle≤1%

## Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	625	°C/W

<sup>\*</sup> Mounted on recommended land-pattern.

<sup>\*2</sup> Mounted on recommended land-pattern.

# ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±10	μA	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D=-1$ mA, $V_{GS}=0$ V
Zero gate voltage drain current	I <sub>DSS</sub>	ı	-	-1	μA	$V_{DS}$ =-30V, $V_{GS}$ =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-1	-	-2.5	V	$V_{DS}$ =-10V, $I_{D}$ =-1mA
		ı	0.9	1.4		$I_D = -0.25A, V_{GS} = -10V$
Static drain-source on-state resistance	R <sub>DS (on)</sub>	-	1.4	2.1	Ω	I <sub>D</sub> =-0.15A, V <sub>GS</sub> =-4.5V
rociotarios		-	1.6	2.4		I <sub>D</sub> =-0.15A, V <sub>GS</sub> =-4V
Forward transfer admittance	IY <sub>fs</sub> †	0.2	-	-	S	$V_{DS} = -10V, I_{D} = -0.15A$
Input capacitance	C <sub>iss</sub>	ı	30	-	pF	V <sub>DS</sub> =-10V
Output capacitance	C <sub>oss</sub>	ı	10	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	$C_{rss}$	-	5	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	-	4	-	ns	V <sub>DD</sub> ≒ -15V, I <sub>D</sub> =-0.15A
Rise time	t <sub>r</sub> *	-	6	-	ns	V <sub>GS</sub> =-10V
Turn-off delay time	t <sub>d(off)</sub> *	-	20	-	ns	R <sub>L</sub> ≒100Ω
Fall time	t <sub>f</sub> *	-	23	-	ns	$R_G=10\Omega$

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V <sub>SD</sub> *	-	-	-1.2	V	$I_s=-0.1A$ , $V_{GS}=0V$

<sup>\*</sup>Pulsed

### ●Electrical characteristic curves (Ta=25°C)

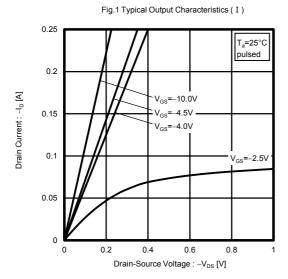


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

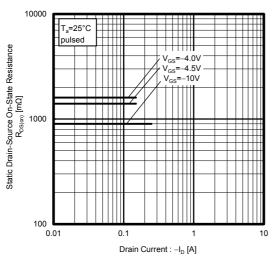


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

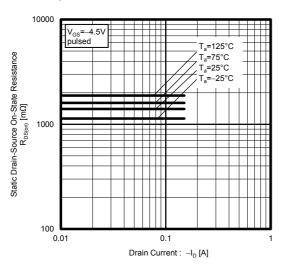


Fig.2 Typical Output Characteristics ( II )

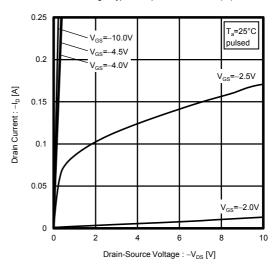


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

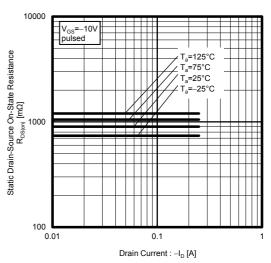


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

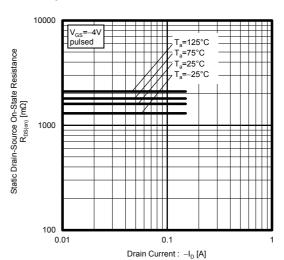


Fig.7 Forward Transfer Admittance vs. Drain Current

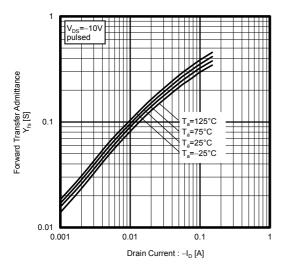


Fig.9 Source Current vs. Source-Drain Voltage

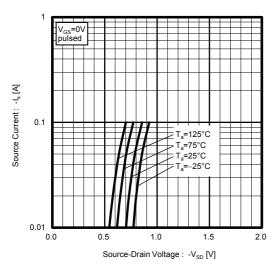


Fig.11 Switching Characteristics

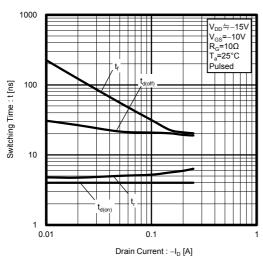


Fig.8 Typical Transfer Characteristics

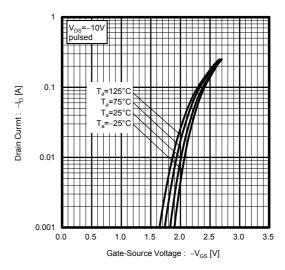


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

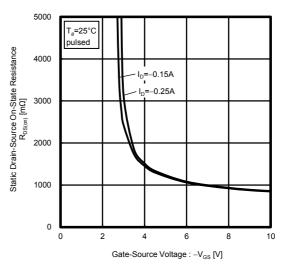
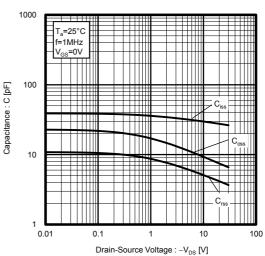


Fig.12 Typical Capacitance vs. Drain-Source Voltage



# Measurement circuits

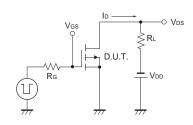


Fig.1-1 Switching Time Measurement Circuit

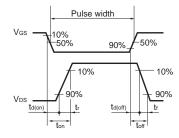


Fig.1-2 Switching Waveforms

### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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